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Erratum: “Reduction of Efficiency Droop in Semipolar (1 $\bar{1}$ 01) InGaN/GaN Light Emitting Diodes Grown on Patterned Silicon Substrates”
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We apologize that we made several mistakes in numbering of the author's affiliation assignment, and would like to correct them. We are sorry for any confusion that this may have caused for the readers of Applied Physics Express. The correct author's list and their corresponding institutes are as follows:

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